

ABSTRACT

An imaging element includes a photoelectric conversion element, a readout transistor, an accumulated element, a detection transistor, and a
5 reset transistor. The readout transistor reads a signal charge when a gate potential to be supplied to the gate terminal is changed from a first state to a second state. The detection transistor detects a voltage signal after the gate potential to be supplied to the gate terminal of the readout transistor is changed from the second state to the first state. A reset potential supplied
10 from the reset transistor to the accumulated element has an intermediate potential between the gate potential in the first state that is supplied to the gate terminal of the readout transistor and a predetermined VDD potential.